

Silicon planar diode Rev. 02 — 31 August 2004

Product data sheet



1.1 General description

Planar high performance band-switching diode in a small rectangular SOT23 SMD plastic package.

1.2 Features

- Continuous reverse voltage: max. 35 V
- Continuous forward current: max. 100 mA
- Low diode capacitance: max. 1.0 pF
- Low diode forward resistance: max. 0.7Ω .

1.3 Applications

Band switching.

Pinning information 2.

Table 1: **Pinning**

Pin	Description	Simplified outline	Symbol		
1	anode		_		
2	not connected	3	3		
3	cathode	1 2	12 sym044		

Ordering information 3.

Table 2: Ordering information

Type number	Package		
	Name	Description	Version
BAT18	-	plastic surface mounted package; 3 leads	SOT23





4. Marking

Table 3: Marking

Type number	Marking code [1]
BAT18	10*

- [1] * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China.

5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	continuous reverse voltage		-	35	V
I _F	continuous forward current		-	100	mA
T _{stg}	storage temperature		–55	+125	°C
Tj	junction temperature		-	125	°C

6. Thermal characteristics

Table 5: Thermal characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

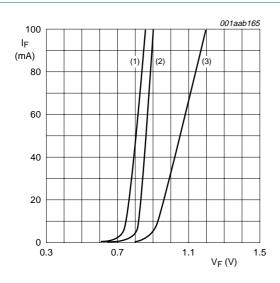
Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-tp)}$	thermal resistance from junction to tie-point		330	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[<u>1</u>] 500	K/W

^[1] Device mounted on a FR4 printed-circuit board.

7. Characteristics

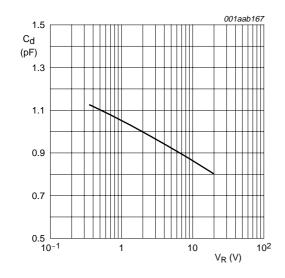
Table 6: Electrical characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I _F = 100 mA; see <u>Figure 1</u>	-	-	1.2	V
I _R	reverse current	see Figure 2				
		V _R = 20 V	-	-	100	nA
		V _R = 20 V; T _j = 60 °C	-	-	1	μΑ
C _d	diode capacitance	V _R = 20 V; f = 1 MHz; see <u>Figure 3</u>	-	8.0	1.0	pF
r _D	diode forward resistance	I _F = 5 mA; f = 200 MHz; see <u>Figure 4</u>	-	0.5	0.7	Ω



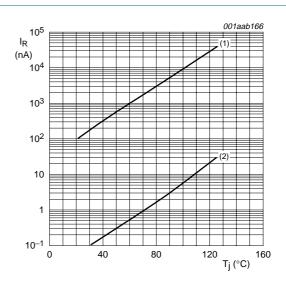
- (1) $T_i = 60 \,^{\circ}\text{C}$; typical values.
- (2) T_i = 25 °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig 1. Forward current as a function of forward voltage.



f = 1 MHz; $T_i = 25 \,^{\circ}\text{C}$.

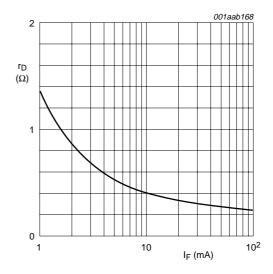
Fig 3. Diode capacitance as a function of reverse voltage; typical values.



 $V_R = 20 \text{ V}.$

- (1) maximum values.
- (2) typical values.

Fig 2. Reverse current as a function of junction temperature.



f = 200 MHz; $T_i = 25 \,^{\circ}\text{C}$.

Fig 4. Diode forward resistance as a function of forward current; typical values.

Package outline

Plastic surface mounted package; 3 leads

SOT23

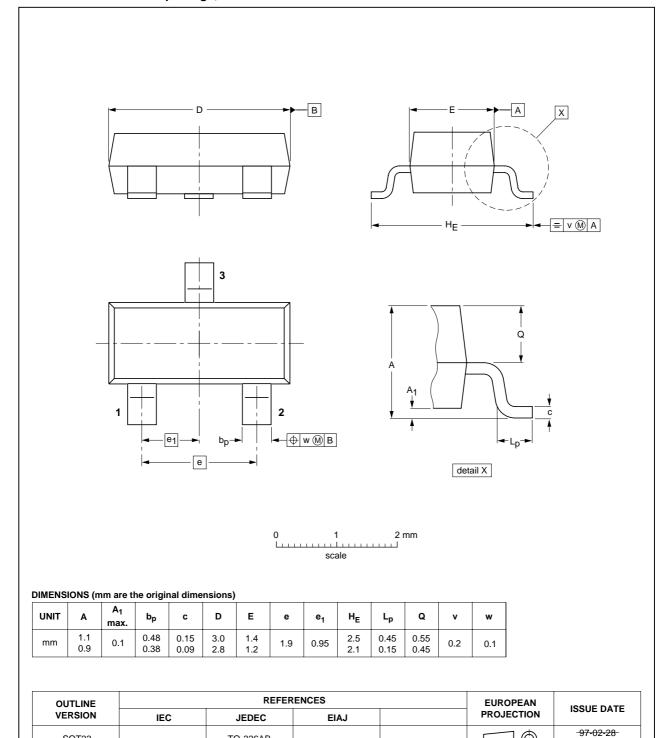


Fig 5. Package outline.

SOT23

99-09-13

TO-236AB

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9. Revision history

Table 7: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BAT18_2	20040831	Product data sheet	-	9397 750 13385	BAT18_1
Modifications: • The format of this data sheet has been redesigned to comply with the new presentat information standard of Philips Semiconductors.		v presentation and			
	• <u>Table 3</u> : m	arking code changed.			
BAT18_1	19960313	Product specification	-	not applicable	-

Philips Semiconductors

BAT18

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10. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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13. Contact information

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